

Notice of References Cited

Application/Control No.

09/840,600

Applicant(s)/Patent Under
Reexamination
TSAI, ROGER S.

Examiner

Thien F Tran

Art Unit

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
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FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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